Olivier Latry

List of Publications by Year
in descending order

72	380	1163117 8	888059 17
papers	citations	h-index	g-index

72	72	72	343
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Dopant activity for highly in-situ doped polycrystalline silicon: hall, XRD, scanning capacitance microscopy (SCM) and scanning spreading resistance microscopy (SSRM). Nano Express, 2021, 2, 010037.	2.4	2
2	Reliability Assessment Of AlGaN/GaN HEMTs on the SiC Substrate Under the RF Stress. IEEE Transactions on Power Electronics, 2021, 36, 7442-7450.	7.9	11
3	Reliability and failure analysis in power GaN-HEMTs during S-band pulsed-RF operating. Microelectronics Reliability, 2021, 126, 114295.	1.7	1
4	Estimation of losses of GaN HEMT in power switching applications based on experimental characterization. Computers and Electrical Engineering, 2020, 84, 106622.	4.8	1
5	Investigation of the aging of power GaN HEMT under operational switching conditions, impact on the power converters efficiency. Microelectronics Reliability, 2019, 100-101, 113403.	1.7	4
6	S-band pulsed-RF operating life test on AlGaN/GaN HEMT devices for radar application. Microelectronics Reliability, 2019, 100-101, 113434.	1.7	7
7	Internal Temperature Measurement of Electronic Components. , 2019, , 169-188.		0
8	Evidence of Mg Segregation to Threading Dislocation in Normally-Off GaN-HEMT. IEEE Nanotechnology Magazine, 2019, 18, 995-998.	2.0	9
9	Thermal Analysis of AlGaN/GaN High-Electron Mobility Transistors Using Iâ€“V Pulsed Characterizations and Infra Red Microscopy. IEEE Transactions on Device and Materials Reliability, 2019, 19, 704-710.	2.0	3
10	Failure investigation of packaged SiC-diodes after thermal storage in extreme operating condition. Engineering Failure Analysis, 2018, 83, 185-192.	4.0	4
11	Modeling of Power GaN HEMT for Switching Circuits Applications Using Levenberg-Marquardt Algorithm. , 2018, , .		6
12	Temperature estimation of high-electron mobility transistors AlGaN/GaN. , 2018, , .		2
13	SiC MOSFET robustness to ESD study: Correlation between electrical and spectral photo-emission characterizations. , 2018, , .		2
14	Optimizing Atom Probe Analysis with Synchronous Laser Pulsing and Voltage Pulsing. Microscopy and Microanalysis, 2017, 23, 221-226.	0.4	4
15	Extraction of physical Schottky parameters using the Lambert function in Ni/AlGaN/GaN HEMT devices with defined conduction phenomena. Journal of Semiconductors, 2017, 38, 014007.	3.7	6
16	Characterization of ESD stress effects on SiC MOSFETs using photon emission spectral signatures. , 2017, , .		4
17	Characterization of HTRB stress effects on SiC MOSFETs using photon emission spectral signatures. Microelectronics Reliability, 2017, 76-77, 243-248.	1.7	7
18	Localizing and analyzing defects in AlGaN/GaN HEMT using photon emission spectral signatures. Engineering Failure Analysis, 2017, 81, 69-78.	4.0	5

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19	Short-circuit robustness test and in depth microstructural analysis study of SiC MOSFET. Microelectronics Reliability, 2017, 76-77, 527-531.	1.7	18
20	Reliability and Qualification Tests for High-Power MOSFET Transistors. , 2017, , 155-197.		1
21	Reliability Study of High-Power Mechatronic Components by Spectral Photoemission Microscopy. , 2017, , 241-271.		5
22	RF Pulse Signal Integrity Analysis for Nonlinear Ended Microstrip Line Atom-Probe Tomography. IOP Conference Series: Materials Science and Engineering, 2016, 120, 012006.	0.6	2
23	Ageing of GaN HEMT devices: which degradation indicators?. Journal of Semiconductors, 2016, 37, 014001.	3.7	8
24	Gate oxide degradation of SiC MOSFET under short-circuit aging tests. Microelectronics Reliability, 2016, 64, 415-418.	1.7	24
25	Effects of drain quiescent voltage on the ageing of AlGaN/GaN HEMT devices in pulsed RF mode. Microelectronics Reliability, 2016, 64, 585-588.	1.7	4
26	Study of different algorithms and models for trapping effect extraction. , 2016, , .		0
27	Electrical and Physical Analysis of Thermal Degradations of AlGaN/GaN HEMT Under Radar-Type Operating Life. IEEE Transactions on Microwave Theory and Techniques, 2016, , 1-11.	4.6	6
28	Reliability Study of Mechatronic Power Components Using Spectral Photon Emission Microscopy. Advanced Electromagnetics, 2016, 5, 20.	1.0	2
29	RF transient pulse signal integrity with ns-duration for atom-probe tomography. , 2015, , .		2
30	Physical Defects Analysis of Mechatronic Systems. , 2015, , 49-77.		0
31	An athermal measurement technique for long time constants traps characterization in GaN HEMT transistors. Microelectronics Reliability, 2015, 55, 1703-1707.	1.7	6
32	High-Efficiency Architecture for Power Amplifiers. , 2015, , 217-241.		0
33	Aging Power Transistors in Operational Conditions. , 2015, , 23-48.		0
34	A workbench development for L-band LDMOS amplifier reliability study (electronic power transistors) Tj ETQq0 0 0 rgBT /Overlock 10 Tf		1
35	Leakage current effects on N-MOSFETs after thermal ageing in pulsed life tests. Microelectronics Journal, 2014, 45, 1800-1805.	2.0	3
36	Channel temperature estimation of AlGaN/GaN HEMT for pulsed RADAR applications using infrared thermography and electrical characterization. , 2014, , .		1

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37	Robustness of 4H-SiC 1200V Schottky diodes under high electrostatic discharge like human body model stresses: An in-depth failure analysis. Diamond and Related Materials, 2014, 44, 62-70.	3.9	9
38	Performance drifts of N-MOSFETs under pulsed RF life test. Microelectronics Reliability, 2014, 54, 1851-1855.	1.7	6
39	Compared deep class-AB and class-B ageing on AlGaN/GaN HEMT in S-Band pulsed-RF operating life. Microelectronics Reliability, 2012, 52, 2561-2567.	1.7	11
40	Physical analysis of Schottky contact on power AlGaN/GaN HEMT after pulsed-RF life test. Microelectronics Reliability, 2012, 52, 2205-2209.	1.7	15
41	Simultaneous measures of temperature and expansion on electronic compound. , 2011, , .		2
42	Adding channels with PSBT format at 40Gbit/s in an existing 10Gbit/s optical network. Optics Communications, 2011, 284, 5125-5129.	2.1	0
43	Characterization and modeling of hot carrier injection in LDMOS for L-band radar application. Microelectronics Reliability, 2011, 51, 1289-1294.	1.7	7
44	A 5000h RF life test on 330 W RF-LDMOS transistors for radars applications. Microelectronics Reliability, 2010, 50, 1574-1576.	1.7	13
45	Characterization of the chirp in semiconductor laser under modulation. Materials Science and Engineering C, 2008, 28, 671-675.	7.3	7
46	Comparison of different feedback signals used in one stage PMD compensators for different modulation formats. IEEE Transactions on Communications, 2008, 56, 1722-1728.	7.8	0
47	New approach for thermal investigation of a III – V power transistor. , 2008, , .		1
48	Theoretical Study of Semiconductor Laser under Modulation. AIP Conference Proceedings, 2007, , .	0.4	1
49	Experimental considerations on bandwidth measurement of ultra-fast photoreceptors by optical heterodyning. Measurement: Journal of the International Measurement Confederation, 2007, 40, 406-414.	5.0	1
50	Using MZIs for Optical PSBT Transmissions: Requirements for Thermal Stabilization. ETRI Journal, 2006, 28, 615-620.	2.0	0
51	Enhanced Optical Generation of 42.7 Gbps Phase Shaped Binary Transmission. ETRI Journal, 2006, 28, 826-829.	2.0	1
52	Fiber-based Mach-Zehnder interferometric structures: principles and required characteristics for efficient modulation format conversion. , 2005, , .		2
53	Optical generation of 43 Gbit/s phase-shaped binary transmission format from DPSK signal using 50 GHz periodic optical filter. , 2005, , .		6
54	Processing of complex stimuli and natural scenes in the visual cortex. Current Opinion in Neurobiology, 2004, 14, 468-473.	4.2	113

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55	Achieving an amplitude-modulated optical wave up to 275 GHz for optical components test. , 2003, , .		0
56	CO 2 -laser-beam-based technique for producing optical fiber components. , 2003, 5260, 154.		2
57	Tapered step profile index fiber with varying core index along the propagation axis. , 2003, , .		0
58	PDL estimation in a concatenation of all-fiber passive optical components. , 2003, , .		0
59	Optogeometrical variations along the propagation axis in all fiber passive components. , 2003, 5246, 686.		0
60	Two lasers mixing for generation of a modulated optical wave. , 2003, 4829, 367.		0
61	Generation of an amplitude modulated optical wave up to 275 GHz by laser wave mixing for optical component bandwidth measurement. Optical Engineering, 2002, 41, 1469.	1.0	2
62	<title>Mixing of two 155-um laser waves in millimeter frequency range for optical components test</title>. , 2002, , .		1
63	Achieving of an optical very high frequency modulated wave source using heterodyne technique. Optics Communications, 2002, 202, 81-90.	2.1	7
64	A model for diffusion of beryllium in InGaAs/InP heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 73-76.	3.5	4
65	<title>Microlens fibers fabricated by a melting-tapering process using a CO<formula><inf><roman>2</roman></inf></formula> laser</title>. , 1999, , .		1
66	Optimization of the coupling between a tapered fibre and a p-i-n photodiode. Journal Physics D: Applied Physics, 1995, 28, 1562-1572.	2.8	6
67	Parametric investigations and simulations of ion beam etching and reactive ion etching mechanisms for GaAs compounds. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1994, 28, 383-386.	3.5	1
68	<title>Modelization of field power distribution in specific singlemode optical fiber for optimal coupling in P-I-N photodiode</title>. , 1994, , .		0
69	<title>Field power distribution in variable core radius of optical fiber for optimal coupling with photodiode</title>. , 1994, , .		0
70	<title>Coupling between two optical fibers for stress distributed sensing</title>. , 1993, 2071, 255.		0
71	<title>New pressure optical sensor for distributed sensing</title>. , 1992, 1586, 96.		0
72	LPFG implementation using electrical-arc and micro-deformations. , 0, , .		0